



SD103AWS...SD103CWS

Surface Mount Schottky Barrier Diodes

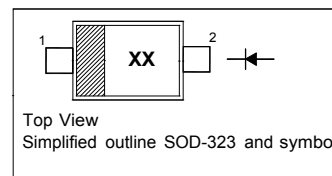
Features

- Low Forward Voltage

Type No.	Marking
SD103AW	S4
SD103BW	S5
SD103CW	S6

PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode



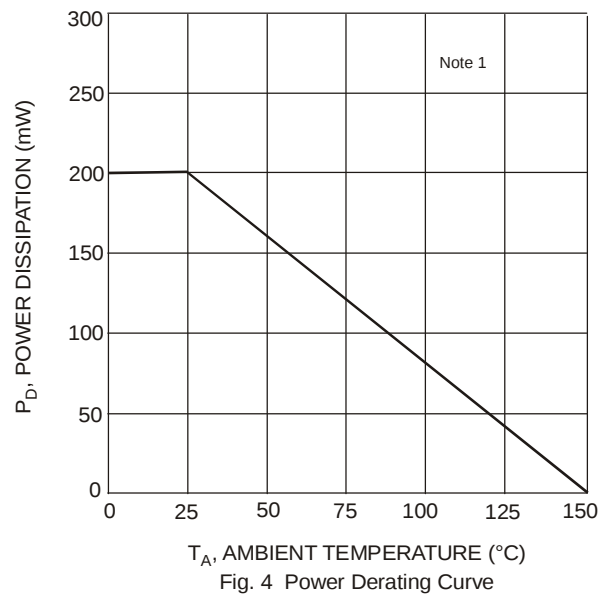
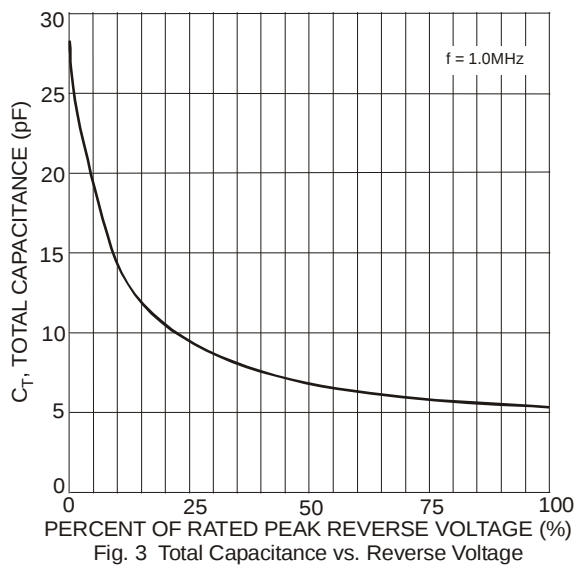
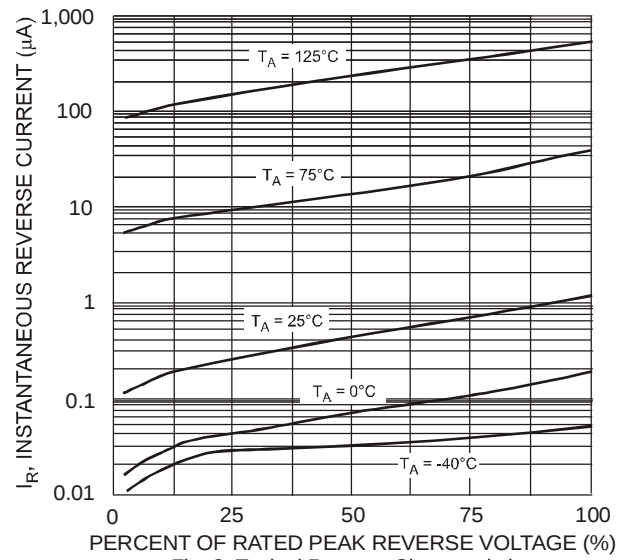
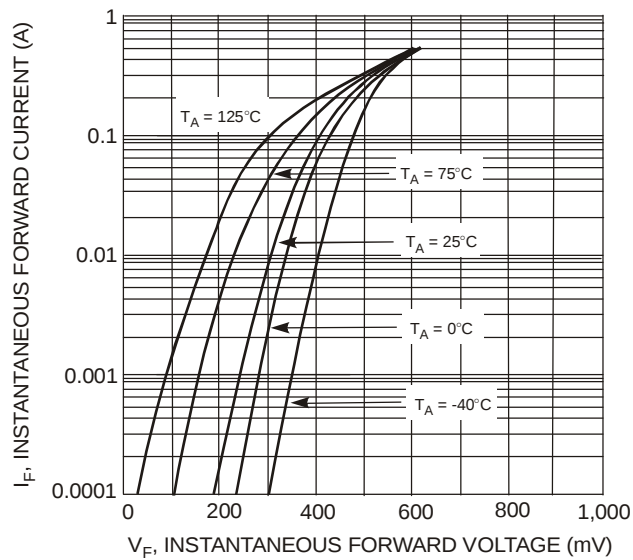
Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Parameter		Symbol	Value	Unit
Peak Repetitive Reverse Voltage	SD103AWS SD103BWS SD103CWS	V_{RRM}	40 30 20	V
Reverse Voltage	SD103AWS SD103BWS SD103CWS	V_R	40 30 20	V
Average Forward Rectified Current		$I_{F(AV)}$	350	mA
Non-Repetitive Peak Forward Surge Current at $t = 1\text{ s}$		I_{FSM}	2	A
Power Dissipation		P_{tot}	200	mW
Operating and Storage Temperature Range		T_j, T_{stg}	- 65 to + 125	$^\circ\text{C}$

Characteristics at $T_a = 25^\circ\text{C}$

Parameter		Symbol	Min.	Typ.	Max.	Unit
Reverse Breakdown Voltage at $I_R = 10\text{ }\mu\text{A}$	SD103AWS SD103BWS SD103CWS	$V_{(BR)R}$	40 30 20	- - -	- - -	V
Reverse Leakage Current at $V_R = 30\text{ V}$ at $V_R = 20\text{ V}$ at $V_R = 10\text{ V}$	SD103AWS SD103BWS SD103CWS	I_R	- - -	- - -	5 5 5	μA
Forward Voltage at $I_F = 20\text{ mA}$ at $I_F = 200\text{ mA}$		V_F	- -	- -	0.37 0.6	V
Total Capacitance at $V_R = 0\text{ V}$, $f = 1\text{ MHz}$		C_T	-	50	-	pF
Reverse Recovery Time at $I_F = I_R = 200\text{ mA}$, $I_{rr} = 0.1 I_R$, $R_L = 100\text{ }\Omega$		t_{rr}	-	10	-	ns

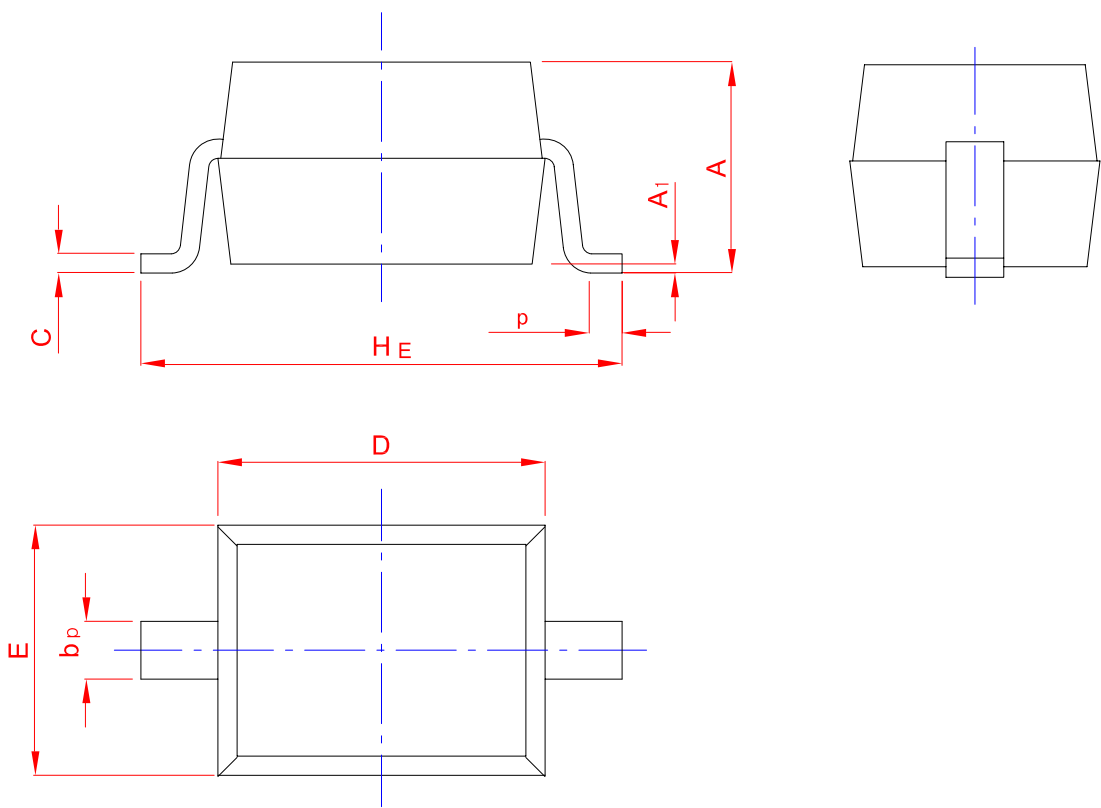
Typical Characteristics



PACKAGE OUTLINE

Plastic surface mounted package; 2 leads

SOD-323



UNIT	A	b _p	C	D	E	H _E	A ₁	L _p
mm	1.20 0.90	0.40 0.25	0.15 0.10	1.80 1.60	1.35 1.15	2.80 2.30	0.10 0.01	0.50 0.20